

STARPOWER

SEMICONDUCTOR™

IGBT

GD200SGU120C2S

Molding Type Module

1200V/200A 1 in one-package

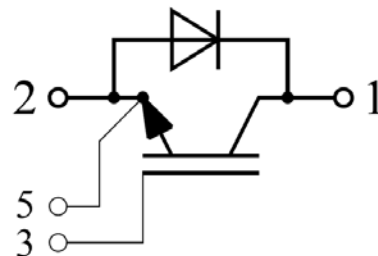
General Description

STARPOWER IGBT Power Module provides ultrafast switching speed as well as short circuit ruggedness. It's designed for the applications such as electronic welder and Inductive heating.



Features

- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- Rugged with ultrafast performance
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

Typical Applications

- Switching mode power supplies
- Inductive heating
- Electronic welder

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Description	GD200SGU120C2S	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^\circ\text{C}$	320	A
	@ $T_C=80^\circ\text{C}$	200	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	400	A
I_F	Diode Continuous Forward Current @ $T_C=80^\circ\text{C}$	200	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	400	A
P_D	Maximum Power Dissipation @ $T_j=150^\circ\text{C}$	1645	W
T_{jmax}	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V
Mounting Torque	Signal Terminal Screw:M4	1.1 to 2.0	N.m
	Power Terminal Screw:M6	2.5 to 5.0	
	Mounting Screw:M6	3.0 to 5.0	

Electrical Characteristics of IGBT $T_C=25^\circ\text{C}$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$T_j=25^\circ\text{C}$	1200			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	4.4	4.9	6.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		3.10	3.55	V
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		3.45		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=200A,$ $R_G=4.7\Omega, V_{GE}=\pm 15V,$ $T_j=25^\circ C$		577		ns
t_r	Rise Time			120		ns
$t_{d(off)}$	Turn-Off Delay Time			540		ns
t_f	Fall Time			123		ns
E_{on}	Turn-On Switching Loss			16.3		mJ
E_{off}	Turn-Off Switching Loss			12.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=200A,$ $R_G=4.7\Omega, V_{GE}=\pm 15V,$ $T_j=125^\circ C$		609		ns
t_r	Rise Time			121		ns
$t_{d(off)}$	Turn-Off Delay Time			574		ns
t_f	Fall Time			132		ns
E_{on}	Turn-On Switching Loss			22.0		mJ
E_{off}	Turn-Off Switching Loss			16.2		mJ
C_{ies}	Input Capacitance	$V_{CE}=30V, f=1MHz,$ $V_{GE}=0V$		16.9		nF
C_{oes}	Output Capacitance			1.51		nF
C_{res}	Reverse Transfer Capacitance			0.61		nF
I_{SC}	SC Data	$t_p \leq 10\mu s, V_{GE}=15V,$ $T_j=125^\circ C, V_{CC}=900V,$ $V_{CEM} \leq 1200V$		1800		A
L_{CE}	Stray Inductance				20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal To Chip			0.18		m Ω

Electrical Characteristics of DIODE $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=200A$	$T_j=25^\circ C$	1.82	2.25	V
			$T_j=125^\circ C$	1.92		
Q_r	Recovered Charge	$I_F=200A,$	$T_j=25^\circ C$	13.1		μC
			$T_j=125^\circ C$	26.1		
I_{RM}	Peak Reverse Recovery Current	$V_R=600V,$ $R_G=4.7\Omega,$	$T_j=25^\circ C$	123		A
			$T_j=125^\circ C$	172		
E_{rec}	Reverse Recovery Energy	$V_{GE}=-15V$	$T_j=25^\circ C$	7.0		mJ
			$T_j=125^\circ C$	12.9		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per IGBT)		0.076	K/W
$R_{\theta JC}$	Junction-to-Case (per DIODE)		0.128	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.035		K/W
Weight	Weight of Module	300		g

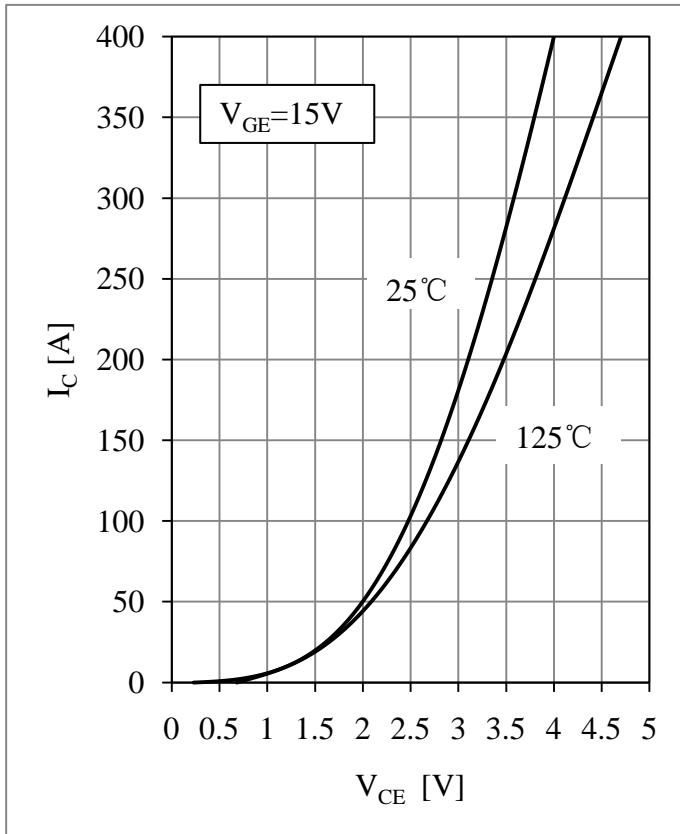


Fig 1. IGBT Output Characteristics

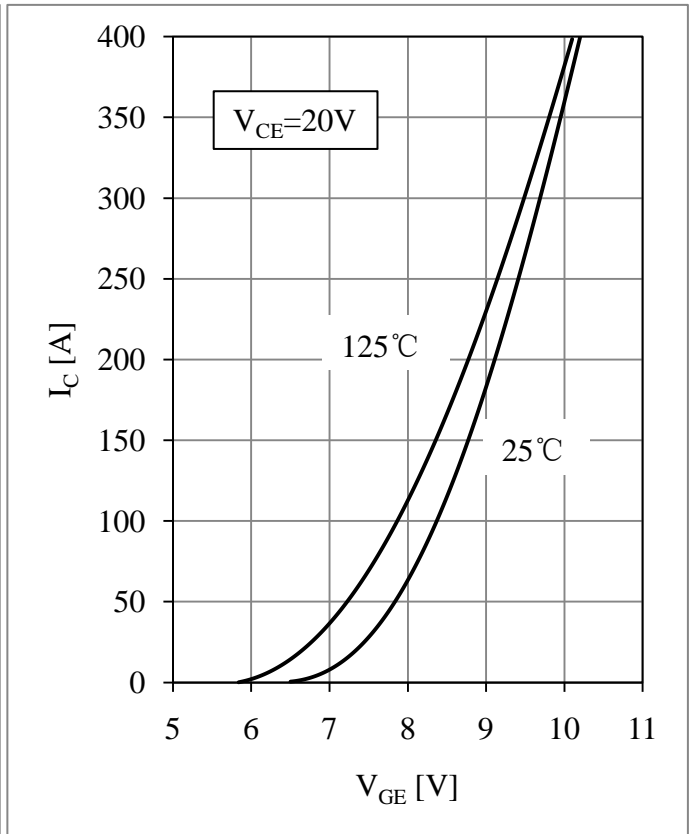


Fig 2. IGBT Transfer Characteristics

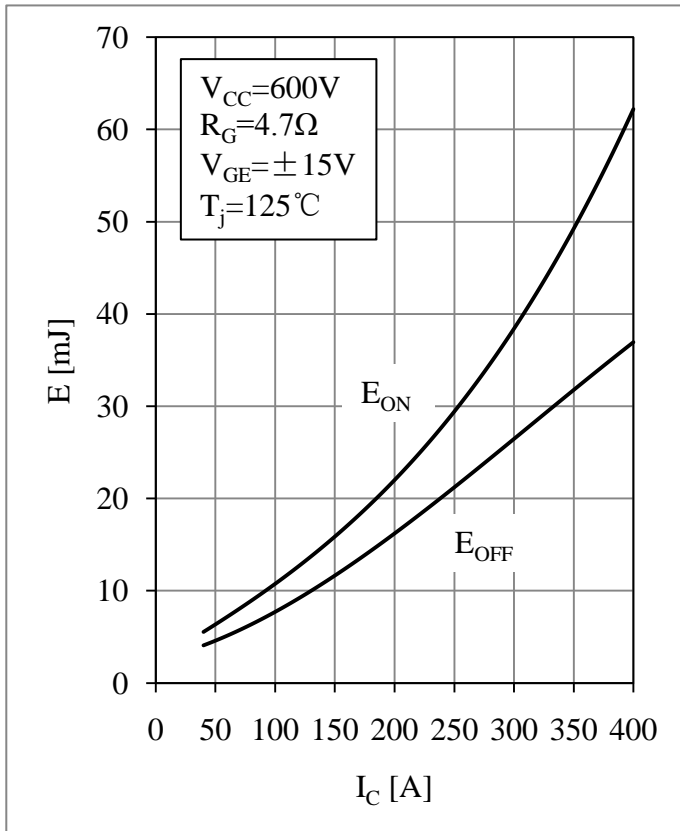


Fig 3. IGBT Switching Loss vs. I_C

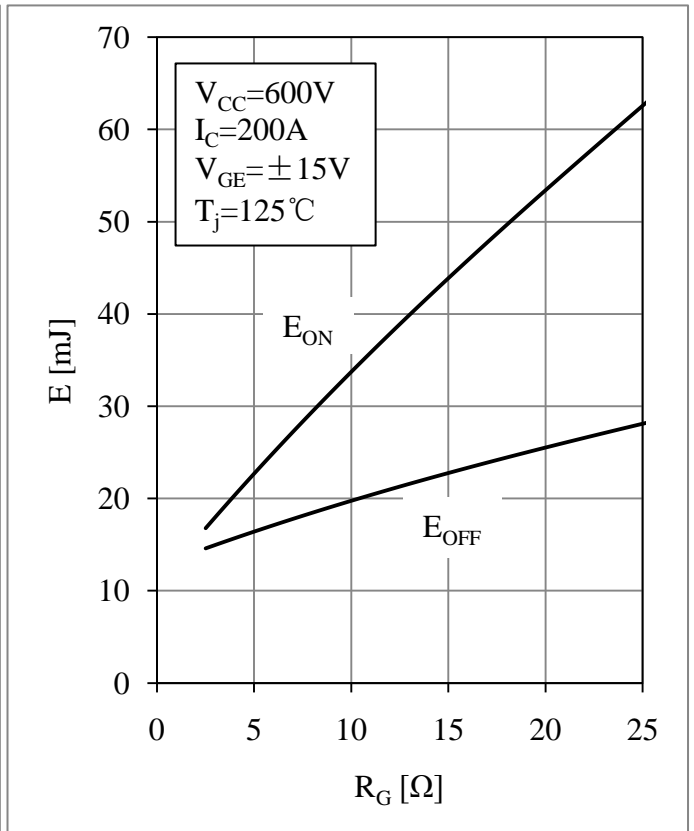


Fig 4. IGBT Switching Loss vs. R_G

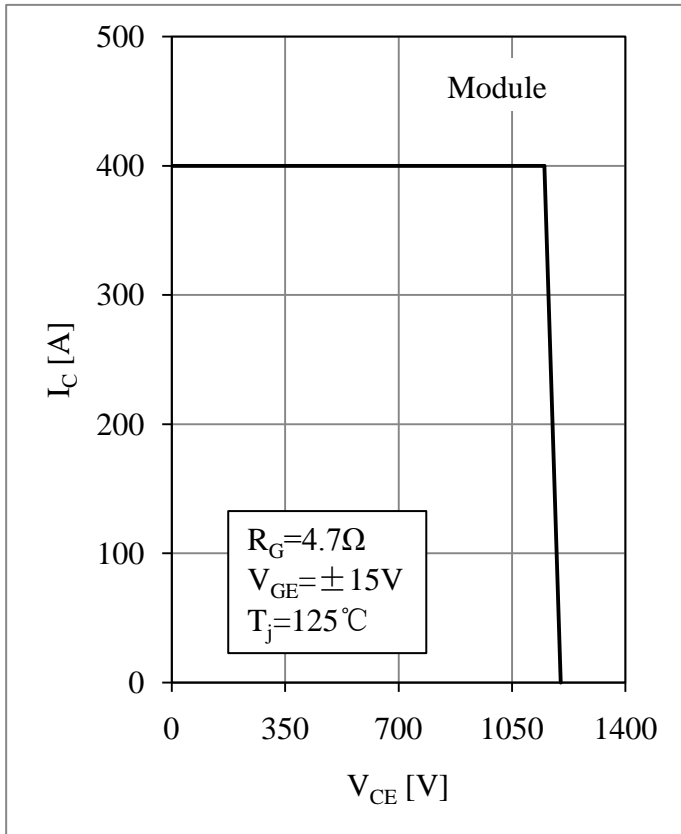


Fig 5. RBSOA

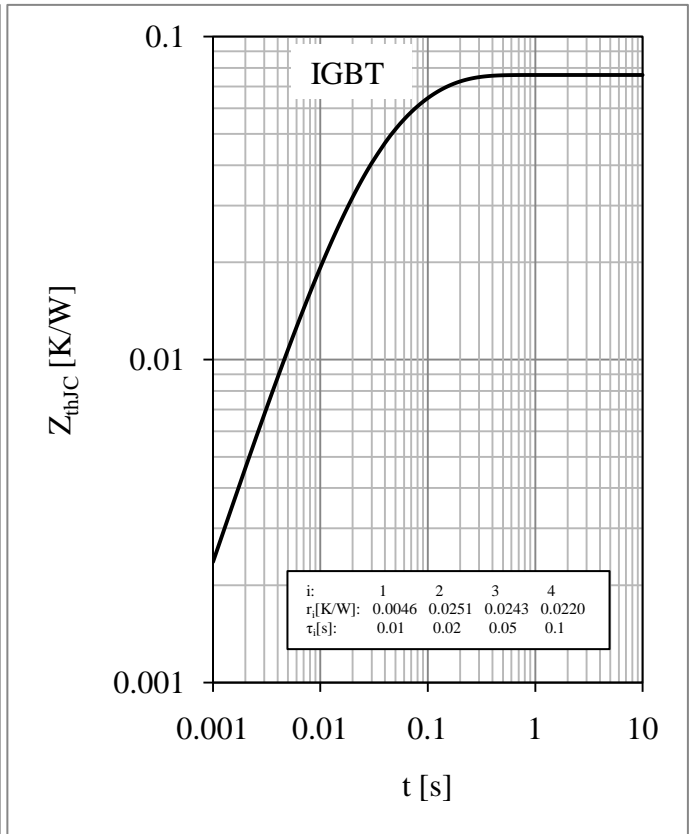


Fig 6. IGBT Transient Thermal Impedance

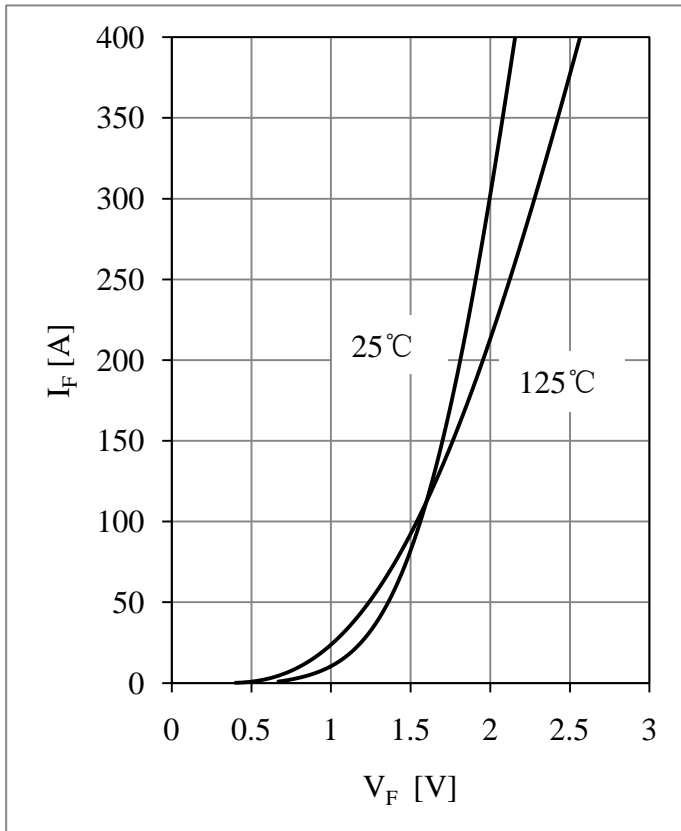


Fig 7. Diode Forward Characteristics

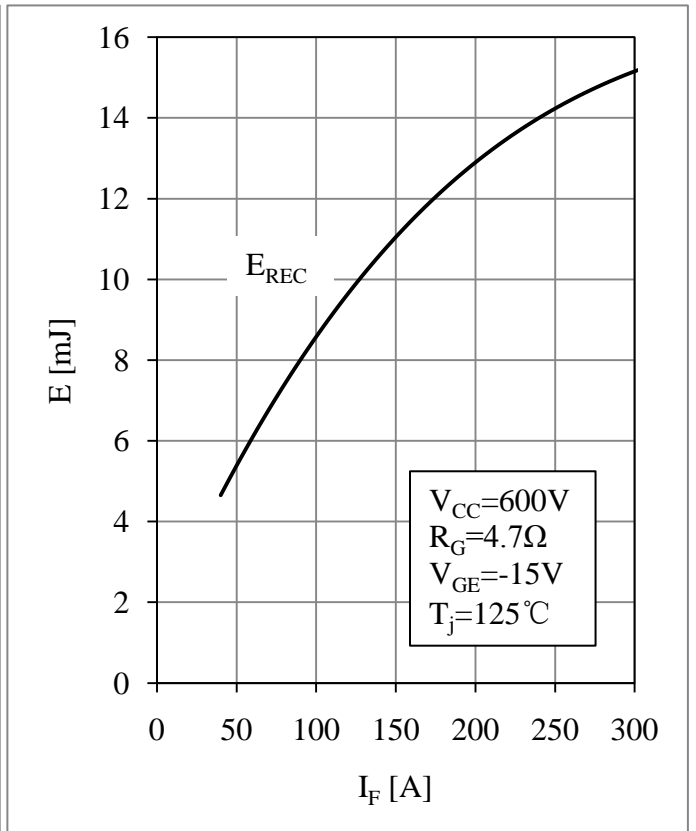


Fig 8. Diode Switching Loss vs. I_F

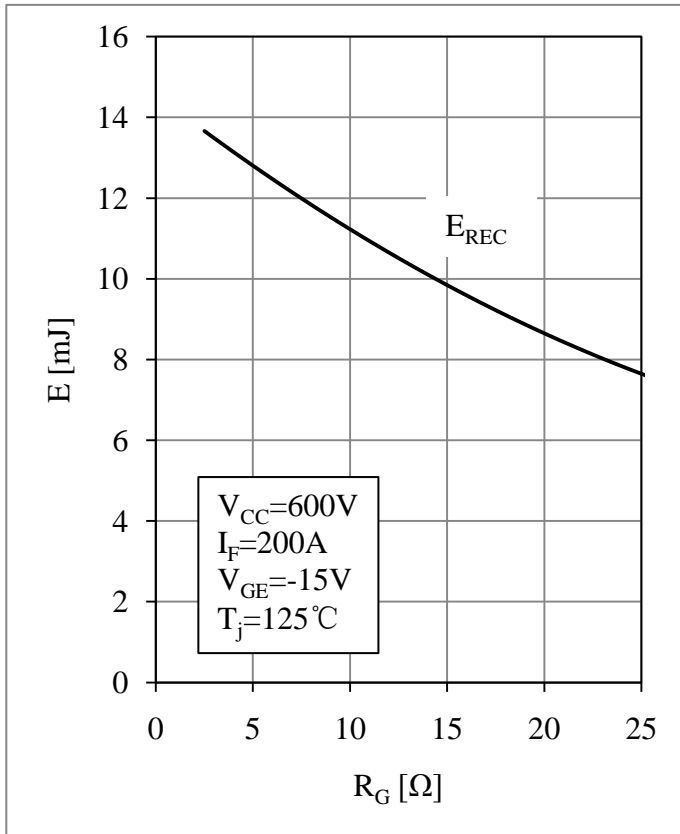


Fig 9. Diode Switching Loss vs. R_G

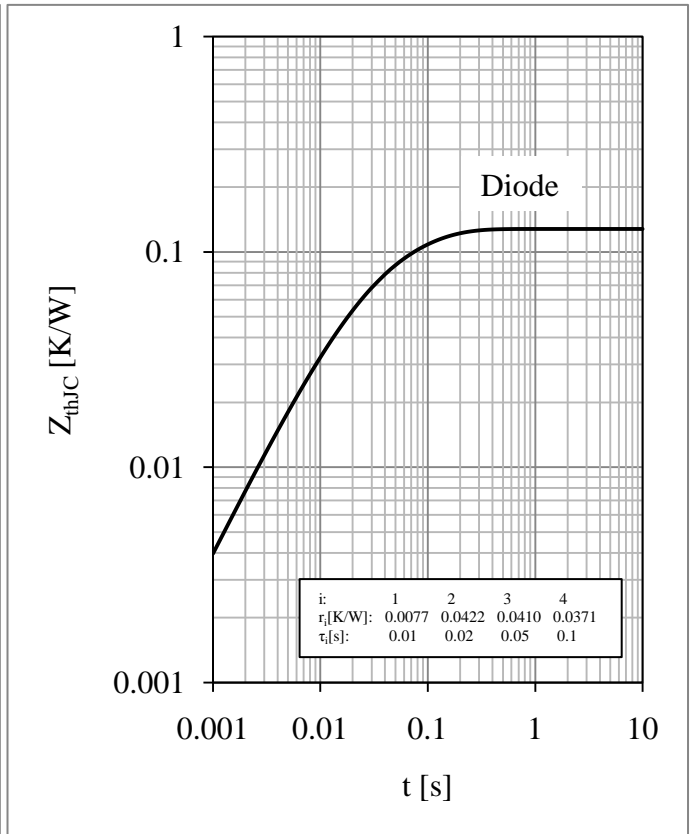


Fig 10. Diode Transient Thermal Impedance

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